

Description

The 5N10 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

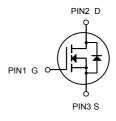


General Features

 $V_{DS} = 100V I_{D} = 5A$

 $R_{DS(ON)}$ < 98 m Ω @ V_{GS} =10V

 $R_{DS(ON)}$ < 120m Ω @ V_{GS} =4.5V



Application

Battery protection

Load switch

Uninterruptible power supply

N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
5N10	SOT23-3L	1005	3000

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit	
VDS	Drain-Source Voltage	100	V	
VGS	Gate-Source Voltage	±20	V	
lo	Drain Current-Continuous	5	Α	
IDM	Drain Current-Pulsed (Note 1)	20	Α	
PD	Maximum Power Dissipation	1.5	W	
TJ,TSTG	Operating Junction and Storage Temperature Range -55		$^{\circ}$	
RθJA	Thermal Resistance,Junction-to-Ambient (Note 2)	100	°C/W	



Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	100	-	-	V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =100V,V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage Current	Igss	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	VGS(th)	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.0	V
		V _{GS} =10V, I _D =3A	-	89	98	mΩ
Drain-Source On-State Resistance	RDS(ON)	V _{GS} =4.5V, I _D =3A	-	102	110	
Forward Transconductance	grs	V _{DS} =5V,I _D =3A	-	5	-	S
Dynamic Characteristics (Note4)						<u>l</u>
Input Capacitance	Clss	V _{DS} =50V,V _{GS} =0V,	-	650	-	PF
Output Capacitance	Coss		-	24	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	20	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	td(on)		-	6	-	nS
Turn-on Rise Time	tr	V _{DD} =50V, R _L =19Ω	-	4	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =3 Ω	-	20	-	nS
Turn-Off Fall Time	tf		-	4	-	nS
Total Gate Charge	Qg		-	20		nC
Gate-Source Charge	Q _{gs}	V_{DS} =50 V , I_{D} =3 A ,	-	2.1	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	3.3	-	nC
Drain-Source Diode Characteristics	l					<u>I</u>
Diode Forward Voltage (Note 3)	VsD	V _{GS} =0V, I _S =3A	-	-	1.2	V
Diode Forward Current (Note 2)	ls		-	-	3	Α

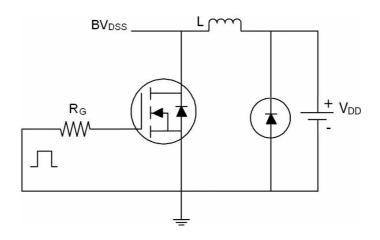
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production

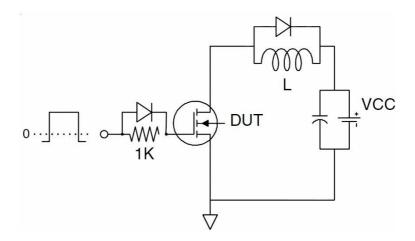


Test Circuit

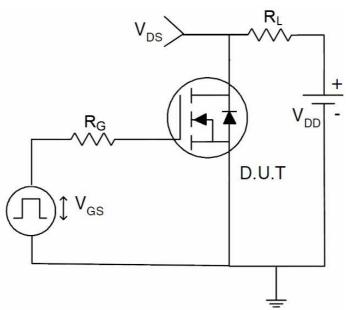
1) E_{AS} test circuit



2) Gate charge test circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

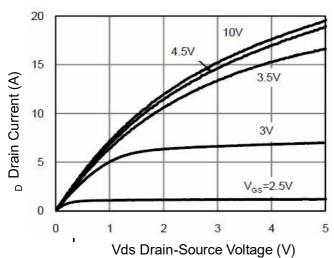


Figure 1 Output Characteristics

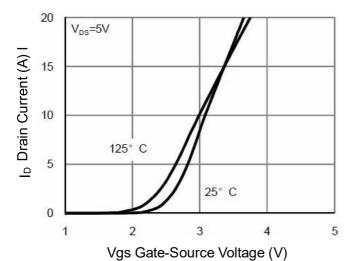


Figure 2 Transfer Characteristics

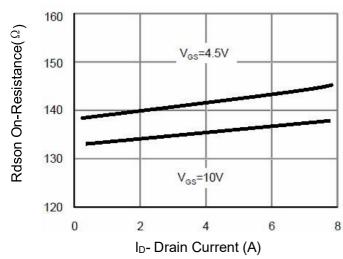


Figure 3 Rdson-Drain Current

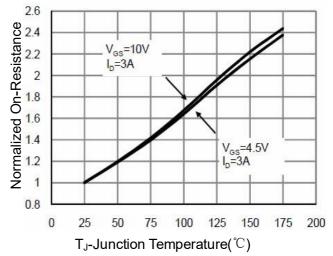


Figure 4 Rdson-JunctionTemperature

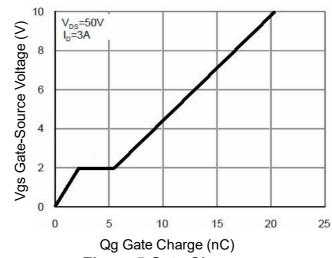


Figure 5 Gate Charge

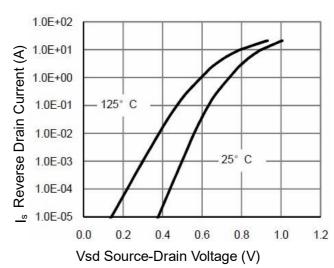
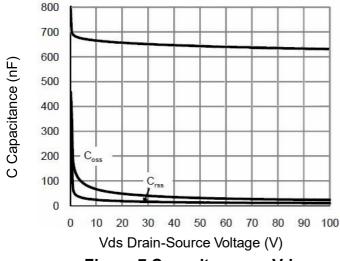
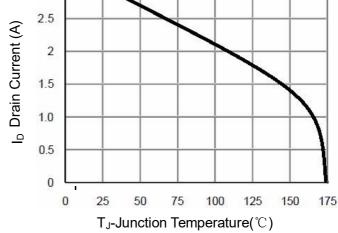


Figure 6 Source-Drain Diode Forward

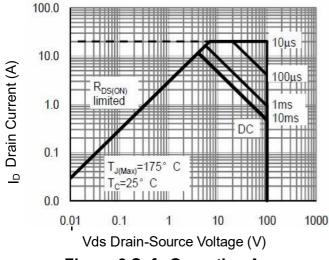




3

Figure 7 Capacitance vs Vds

Figure 9 BV_{DSS} vs Junction Temperature



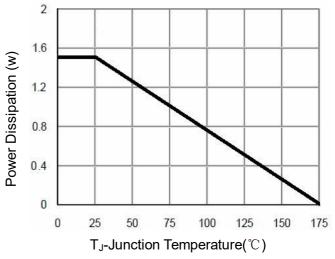
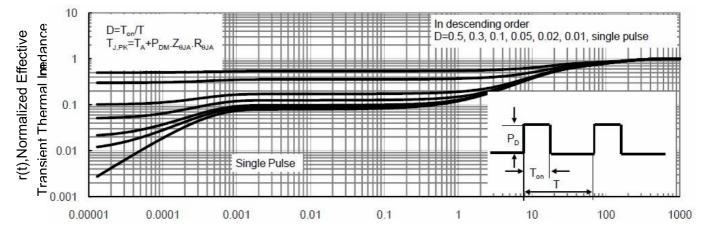


Figure 8 Safe Operation Area

Figure 10 Power De-rating

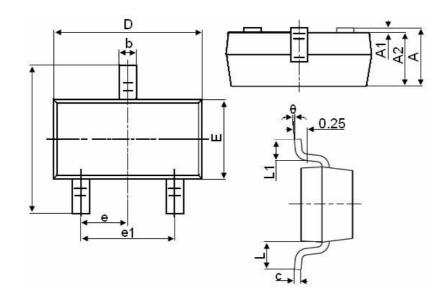


Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



SOT23-3L Package Information



Symbol	Dimensions in Millimeters		
	MIN.	MAX.	
А	1.050	1.250	
A1	0.000	0.100	
A2	1.050	1.150	
b	0.300	0.500	
С	0.100	0.200	
D	2.800	3.000	
E	1.500	1.700	
E1	2.650	2.950	
е		0.950TYP	
e1	1.800	2.000	
L	0.550REF		
L1	0.300	0.600	
θ	0°	8°	



Attention

- Any and all HUA XUAN YANG ELECTRONICS products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your HUA XUAN YANG ELECTRONICS representative nearest you before using any HUA XUAN YANG ELECTRONICS products described or contained herein in such applications.
- HUA XUAN YANG ELECTRONICS assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein.
- Specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- HUA XUAN YANG ELECTRONICS CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all HUA XUAN YANG ELECTRONICS products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of HUA XUAN YANG ELECTRONICS CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production.

 HUA XUAN YANG ELECTRONICS believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the HUA XUAN YANG ELECTRONICS product that you intend to use.